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a light-emitting layer configured to emit light; and
a single reflection layer positioned closer to the substrate than the
light-emitting layer and being configured to reflect light toward a light extracting direction.

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11. (Three Times Amended) A light-emitting apparatus comprising:
a primary light source including a GaN semiconductor light-emitting device with
an emission wavelength of from 380 nm to 500 nm; and
a secondary light source including a fluorescent material including at least one of
ZnS:Eu and Y₂O₂S:Ce,
wherein said secondary light source emits light based on light given from
said primary light source so that light of said secondary light source and the light of said primary
light source are mixed together to thereby generate light different in luminescent color from the
light emitted from said primary light source, and
wherein the GaN semiconductor light-emitting device comprises:
a substrate;
a light-emitting layer configured to emit light; and
a single reflection layer positioned closer to the substrate than the
light-emitting layer and being configured to reflect light toward a light extracting direction.

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21. (Three Times Amended) A light-emitting apparatus comprising:
a first light source including a GaN semiconductor light-emitting device
configured to emit blue light;
a second light source including a first fluorescent material configured to absorb
light of said first light source and to emit green light; and
a third light source including a second fluorescent material configured to absorb
light of said first light source and to emit red light,
wherein the light of said first light source, light of said second light source,
and light of said third light source are mixed together to thereby generate white light.

22. (Twice Amended) A light-emitting apparatus according to claim 21, wherein said first fluorescent material comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu; ZnS:Mn; ZnS:Eu; Y₂O₂S:Eu; and Y₂O₂S:Ce.

Please add claims 38-40 as follows:

38. The light-emitting apparatus according to claim 1, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

39. The light-emitting apparatus according to claim 11, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

40. The light-emitting apparatus according to claim 21, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

REMARKS

Claims 1-22, 25-34, and 38-40 are pending in the application. This Amendment amends claims 1, 11, 21, and 22 and adds claims 38-40. No new matter is added to amended claims 1, 11, 21, and 22.

Claims 1, 11, 21, and 22 are amended to merely clarify the subject matter of the claims and in no way narrow the scope of the claims in order to overcome the prior art or for any other statutory purpose of patentability.

Notwithstanding any claim amendments of the present Amendment or those amendments that may be made later during prosecution, Applicants' intent is to encompass equivalents of all claim elements. Reconsideration in view of the foregoing amendments and the following remarks is respectfully requested.

Attached hereto is a marked-up version of the changes made to the claims by the current Amendment. The attached page is captioned "Version with markings to show changes made."